/ Descriptions

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Schottky Barrier Diode in a R-6 Plastic Package.

/ Features

Rs PRV　⸗ ᵍ Ṫ　Ḩ　ᵇ я ں ı Ḩ ı ᾰ　ﮍ ڹ ' ڟ Φ　ֵ Ꭰ ᒧ □ v533 ɫ ı ꝑ ᶿ ڳ ٲ ' ڽ Ẕ ꞁ ₩
Ã　HVG ٲ ᒣ ڙ　° 63NY

Trench MOS Schottky technology, Low forward voltage drop, low power losses, High efficiency operation, TJ ≤200 °C max. in solar bypass mode application, ESD ability to achieve ±30KV.

/ Applications

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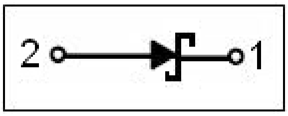
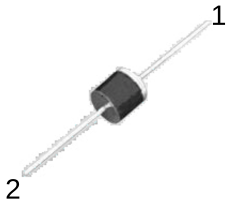
For use in solar cell junction box as a bypass diode for protection, high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

/ Equivalent Circuit



/ Pinning



PIN1 χ Cathode　　　PIN 2 χ Anode

/ h_{FE} Classifications & Marking

ǒ м ٦ ب ˝　See Marking Instructions.

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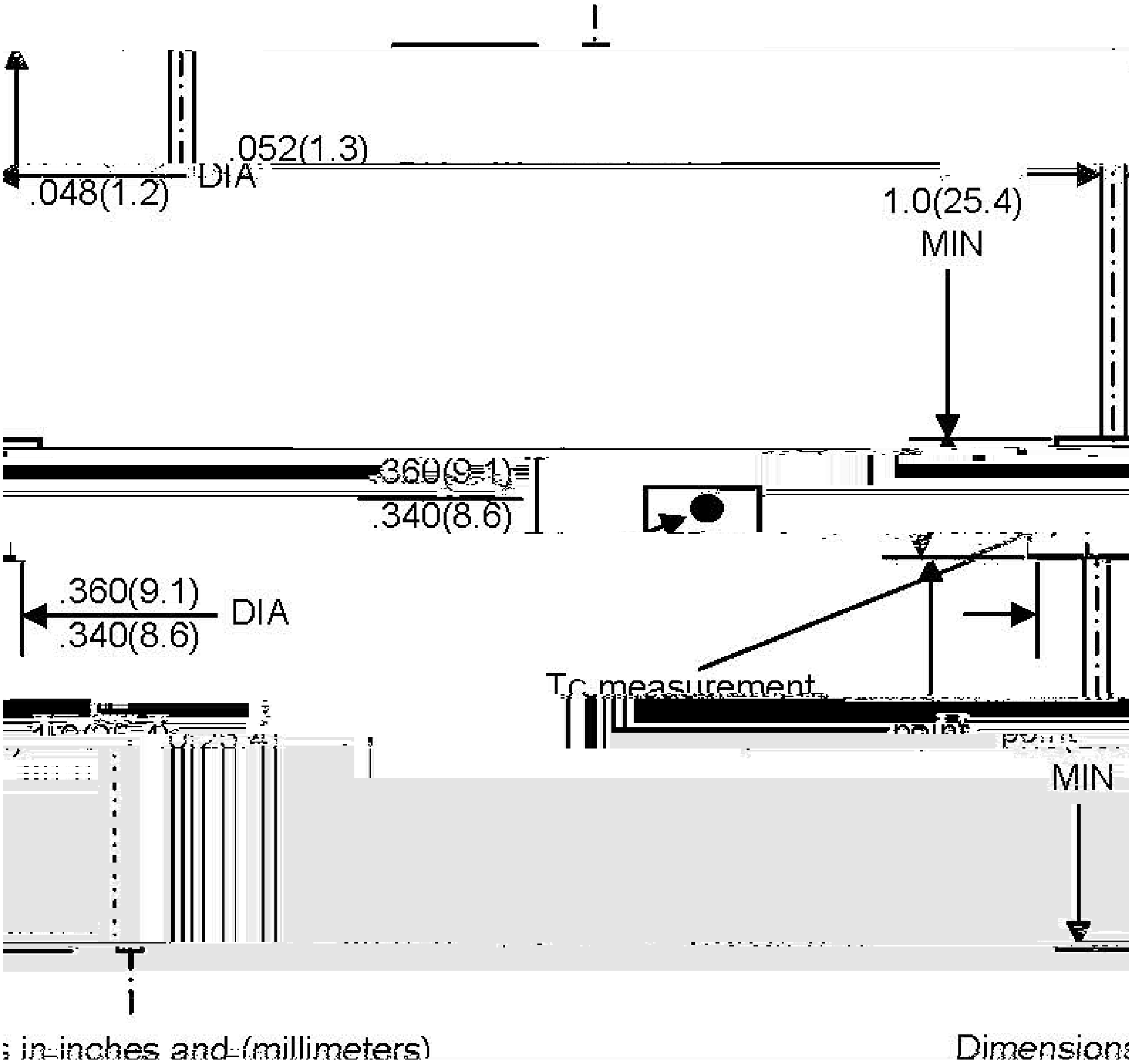
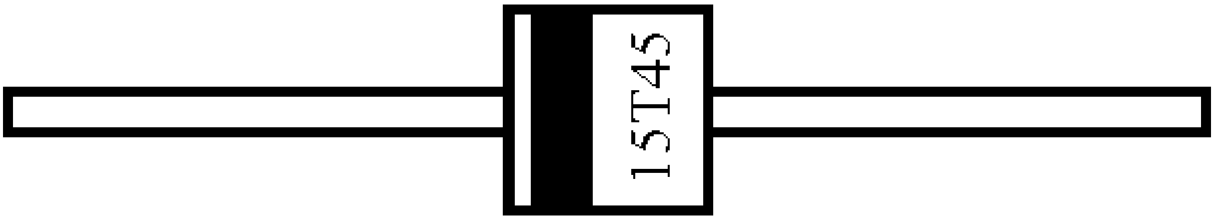
Parameter	Symbol	Rating	Unit

/ Package Dimensions

R-6



/ Marking Instructions



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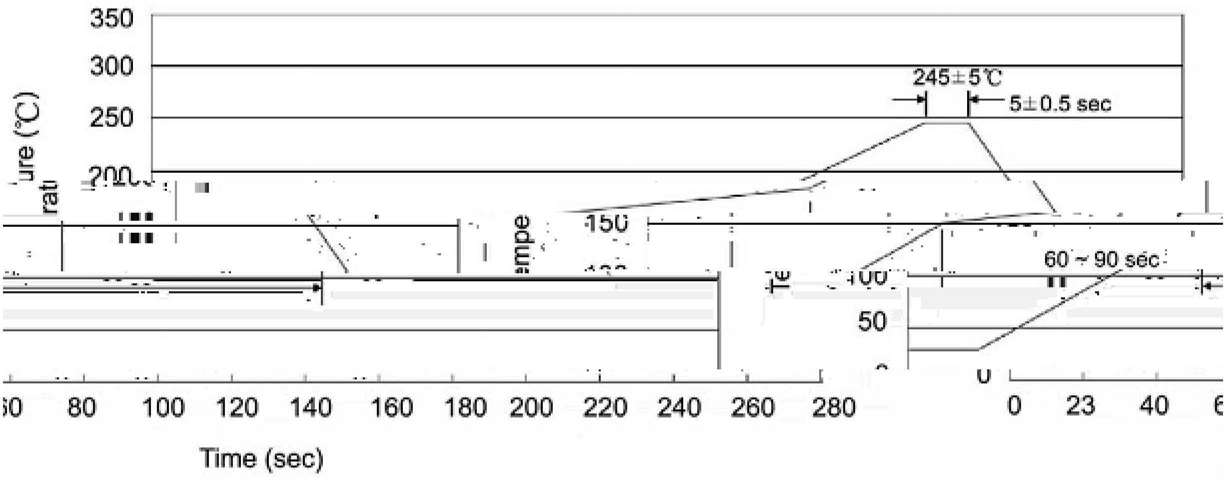
48W78 χ ѭ ᶚ ᴺ Ⴄ

Note:

48W78 χ Product Type Code.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



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1 ỉ ♬ □ ỷ 25 Ḱ 150 ƚ ı ̀H ݽ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ƚ